

Silicon PNP Power Transistors

2SB514

DESCRIPTION

- With TO-220C package
- Complement to type 2SD330
- Low collector saturation voltage

APPLICATIONS

- Suited for use in output stage of 10W AF power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

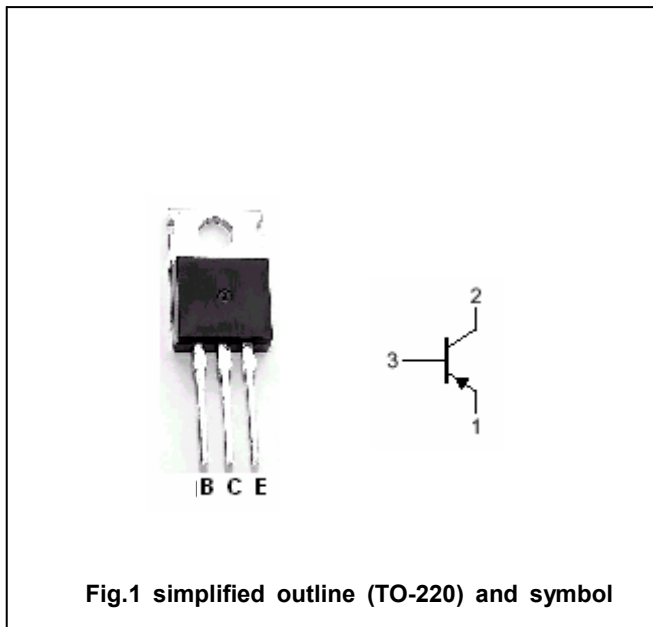


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-50	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current (DC)		-2	A
I _{CM}	Collector current-Peak		-5	A
P _C	Collector dissipation	T _a =25°C	1.75	W
		T _C =25°C	20	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-50~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter voltage	I _C =-10mA; I _B =0	-50			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-0.2A			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-1A; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-20V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-1.0	mA
h _{FE-1}	DC current gain	I _C =-1A; V _{CE} =-2V	40		320	
h _{FE-2}	DC current gain	I _C =-0.1A; V _{CE} =-2V	35			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-5V		8		MHz

◆ h_{FE-1} Classifications

C	D	E	F
40-80	60-120	100-200	160-320

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PACKAGE OUTLINE

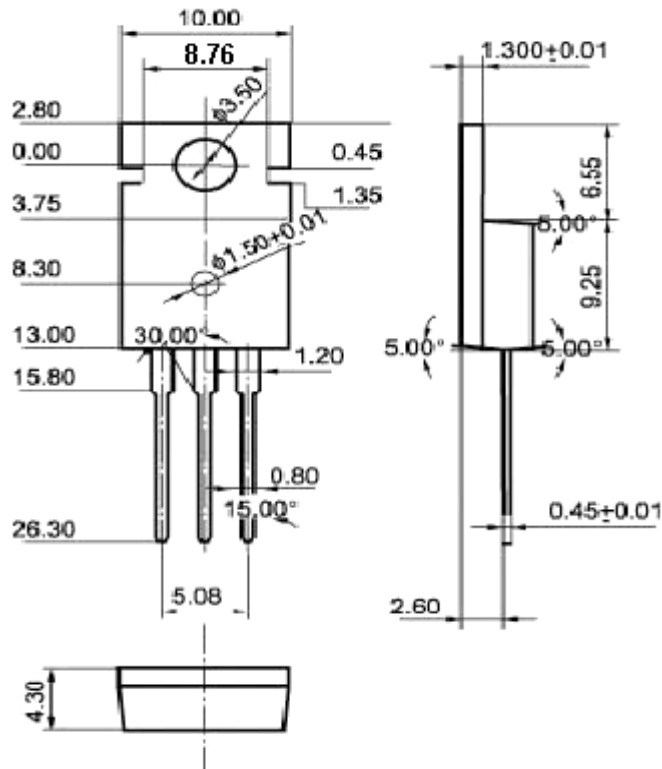


Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)